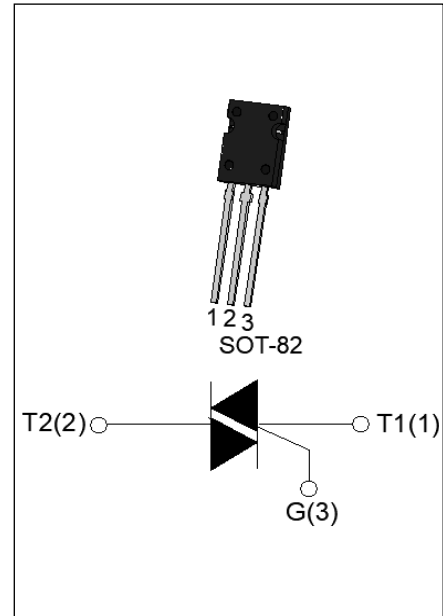


DESCRIPTION:

The JST134QP-800E triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. From T2 terminals to external heatsink. Package SOT-82 is RoHS compliant.


MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	4	A
V_{DRM}/V_{RRM}	800	V
$I_{GT\ I/II/III/IV}$	10/10/10/25	mA

ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40-150	°C
Operating junction temperature range		T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)		V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)		V_{RRM}	800	V
RMS on-state current ($T_c \leq 84^\circ\text{C}$)		$I_{T(RMS)}$	4	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)		I_{TSM}	25	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)			27.5	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)		I^2t	3.125	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	I - II -III	di/dt	70	$\text{A}/\mu\text{s}$
	IV		40	
Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$)		I_{GM}	2	A
Average gate power dissipation ($T_j=125^\circ\text{C}$)		$P_{G(AV)}$	0.5	W
Peak gate power		P_{GM}	5	W
Peak pulse voltage ($T_j=25^\circ\text{C}$; non-repetitive,off-state;FIG.7)		V_{pp}	4	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12\text{V}$ $R_L=33\Omega$	I - II - III	MAX.	10	mA
		IV		25	
V_{GT}		ALL	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	ALL	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I - III - IV	MAX.	15	mA
		II		25	
I_H	$I_T=100\text{mA}$		MAX.	20	mA
dV/dt	$V_D=540\text{V}$ Gate Open $T_j=110^\circ\text{C}$		MIN.	250	$\text{V}/\mu\text{s}$
$(dV/dt)_c$	$(dI/dt)_c=1.8\text{A}/\text{ms}$, $T_j=110^\circ\text{C}$		MIN.	6	$\text{V}/\mu\text{s}$
t_{on}	$I_G=40\text{mA}$ $I_A=200\text{mA}$ $I_R=20\text{mA}$ $T_j=25^\circ\text{C}$		TYP.	3	μs
t_{off}				30	

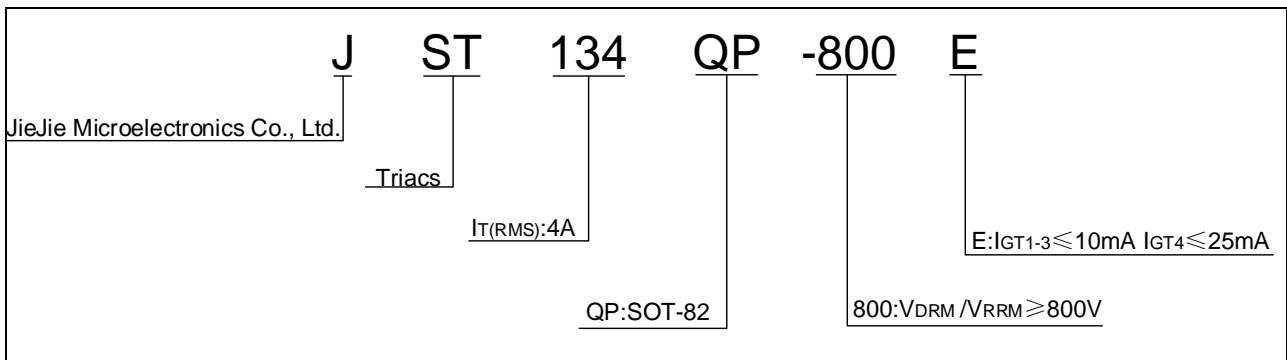
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=5\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.55	V
V_{TO}	Threshold voltage	$T_j=125^\circ\text{C}$	0.92	V
R_D	Dynamic resistance	$T_j=125^\circ\text{C}$	107	$\text{m}\Omega$
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	μA
I_{RRM}		$T_j=125^\circ\text{C}$	0.35	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	7.0	$^\circ\text{C}/\text{W}$
$R_{th(j-a)}$	junction to ambient (AC)	150	$^\circ\text{C}/\text{W}$

ORDERING INFORMATION



MARKING

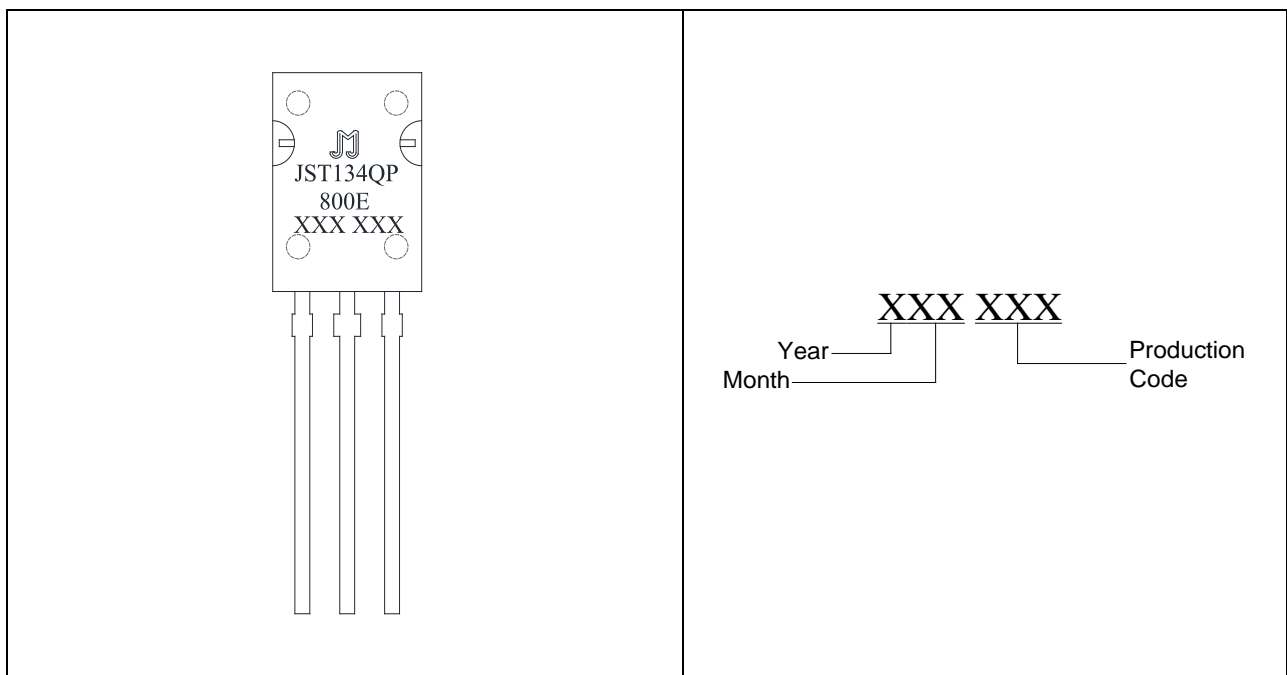


FIG.1 Maximum power dissipation versus RMS on-state current

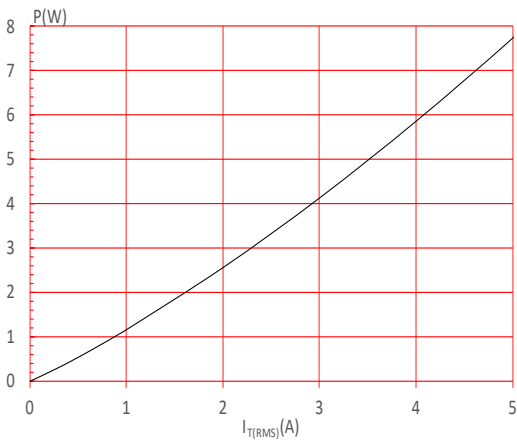


FIG.3: Surge peak on-state current versus number of cycles

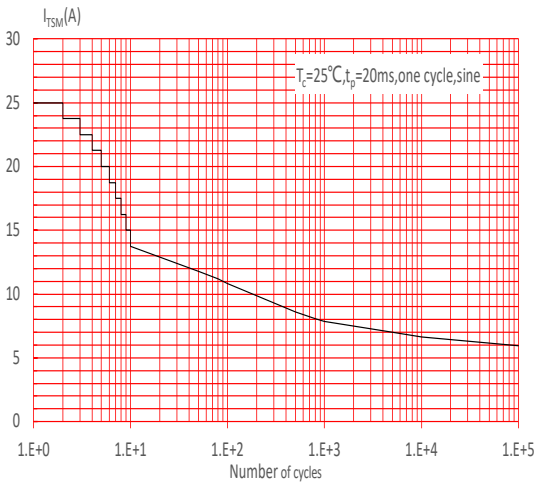


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t (I - II -III: $di/dt < 70\text{A}/\mu\text{s}$; IV: $di/dt < 40\text{A}/\mu\text{s}$)

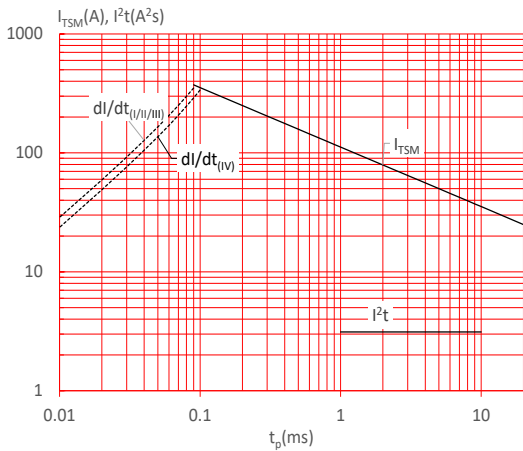


FIG.2: RMS on-state current versus case temperature

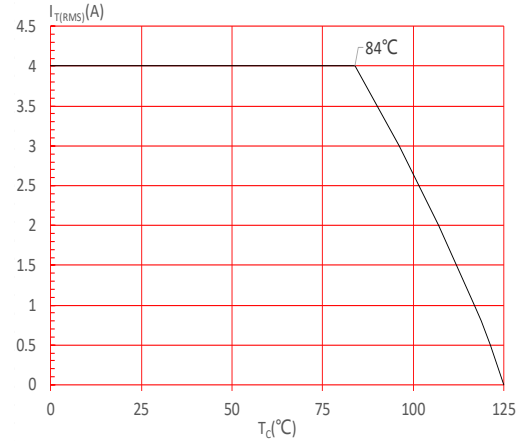


FIG.4: On-state characteristics

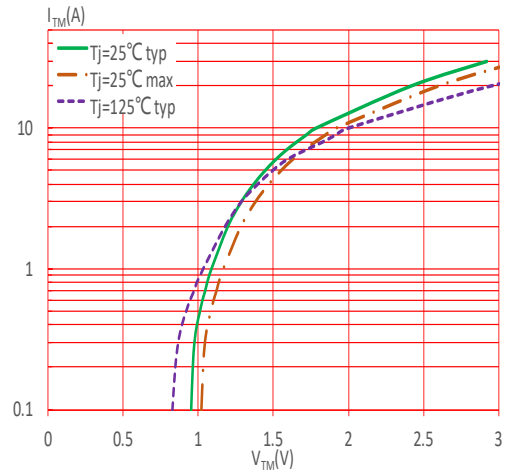


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

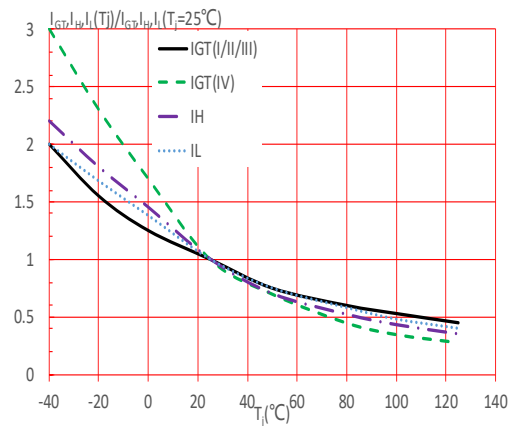
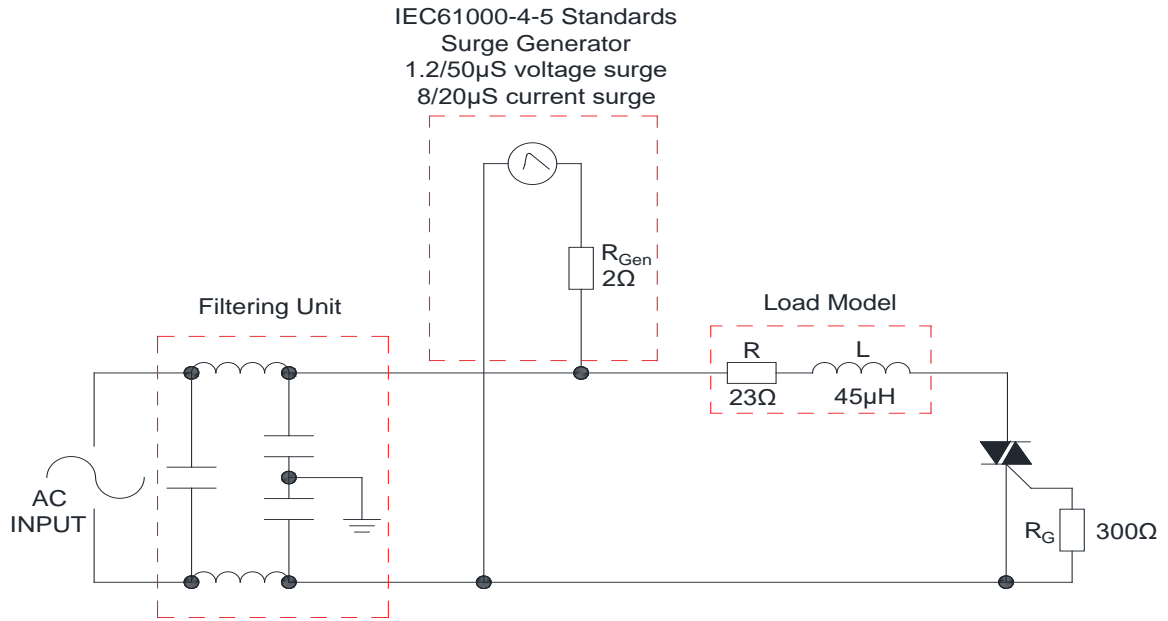


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie.

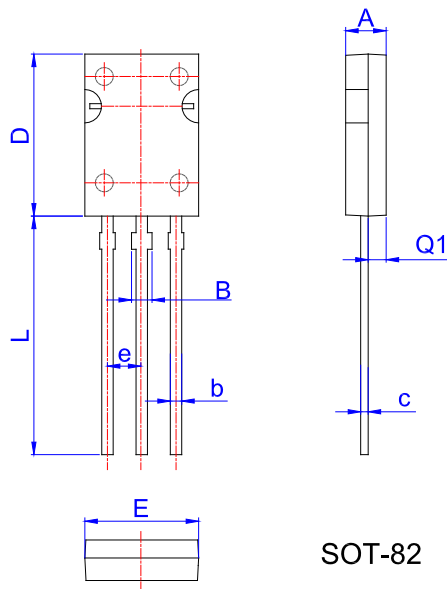
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)		Package	Base qty. (pcs)	Delivery mode
		I -II-III	IV			
JST134QP-800E	800	10	25	SOT-82	500	Bulk Pack

Document Revision History

Date	Revision	Changes
Apr.14, 2023	A.1.0	Last updated

PACKAGE MECHANICAL DATA



SOT-82

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.45	2.55	2.65	0.096	0.100	0.104
b	0.71	0.76	0.81	0.028	0.030	0.032
B	1.27	1.37	1.45	0.050	0.054	0.057
c	0.48	0.50	0.52	0.019	0.020	0.021
D	10.60	10.80	11.00	0.417	0.425	0.433
E	7.30		7.70	0.287		0.303
e	2.24	2.29	2.34	0.088	0.090	0.092
L	15.30	15.60	15.90	0.602	0.614	0.626
Q1	1.17	1.27	1.37	0.046	0.050	0.054

DELIVERY MODE

PACKAGE	OUTLINE	BAG (PCS)	INNER BOX (PCS)	CARTON BOX (PCS)
SOT-82	Bulk Pack	500	2,000	10,000

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